DFS10HF12EZC1

1200V/10mΩ Half Bridge SiC MOSFET Module

Description

The DFS10HF12EZC1 is a Half Bridge SiC MOSFET half bridge Power Module. It integrates high performance SiC MOSFET chips designed for the applications such as Solar Inverter, UPS, Fuel cell- DC/DC converter, Energy storage Systems.

Features

- Blocking voltage:1200V
- 10.1mΩ $R_{ds(on)}$@T_j =25°C
- 160A@T_f =75°C
- Low Switching Losses
- 175°C maximum junction temperature
- Si_3N_4 AMB
- Thermistor inside

Applications

- Solar inverter Systems
- Fuel cell-DC/DC converter
- Uninterruptible Power Supplier
- Energy Storage Systems

Circuit diagram

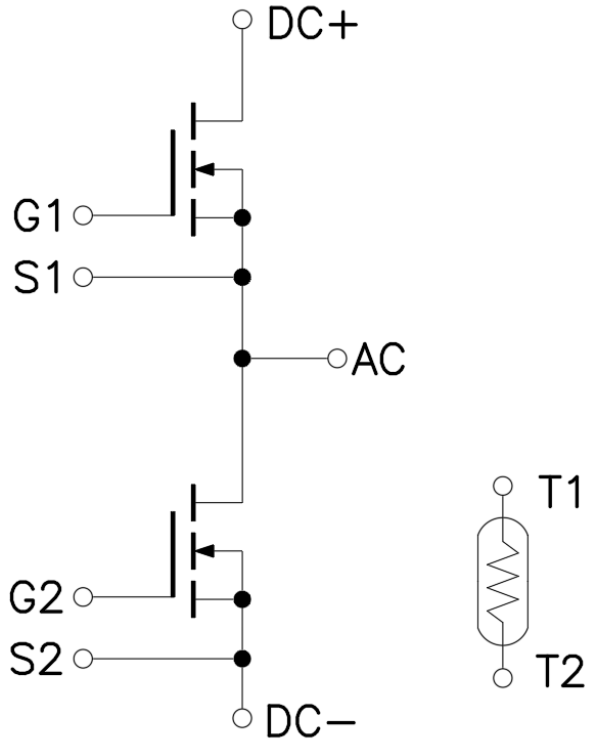


Figure 1. Out drawing & circuit diagram for DFS10HF12EZC1

Pin Configuration and Function Description

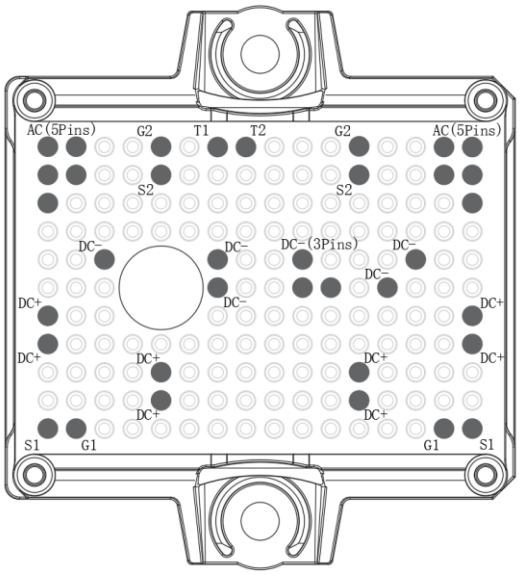


Figure 2. Pin configuration

PIN No.	Symbol	Description
1-5(5pins)	AC	Output terminal of half bridge
6	S2	Low side source signal terminal
7	G2	Low side gate signal terminal
8	T1	Thermistor connection 1
9	T2	Thermistor connection 2
10	S2	Low side source signal terminal
11	G2	Low side gate signal terminal
12-16(5pins)	AC	Output terminal of half bridge
17-24(8pins)	DC –	DC – Bus connection
25-32(8pins)	DC +	DC + Bus connection
33	S1	High side source signal terminal
34	G1	High side gate signal terminal
35	G1	High side gate signal terminal
36	S1	High side source signal terminal

Module

Parameter	Conditions	Value	Unit
Isolation voltage	RMS, f =50Hz, t =1min	3.4	kV
Clearance	Terminal to Terminal	5	mm
	Terminal to Heatsink	10	mm
Creepage distance	Terminal to Terminal	6.3	mm
	Terminal to Heatsink	12.7	mm
Comparative Tracking Index	-	400	-

Maximum Ratings (T_j =25°C unless otherwise specified)

Symbol	Parameter	Conditions	Ratings	Unit
V_{DSS}	Drain-Source Voltage	G-S Short	1200	V
V_{GSS}	G-S Voltage	D-S Short, Note1	-10 to 20	V
I_{DS}	DC Continuous Drain Current	T_f =80°C	160	A
I_{SD}	Source (Body diode) Current	T_f =80°C, with ON signal	160	A
I_{DP}	Drain Pulse Current, Peak	Less than 1ms, Note2	400	A
T_j	junction temperature	-	-40 to 175	°C
T_{stg}	Storage temperature	-	-40 to 125	°C

Note1: Recommended Operating Value, -5V/+15V.

Note2: Pulse width limited by maximum junction temperature

NTC characteristics

Symbol	Parameter	Condition	Value			Unit
			Min.	Typ.	Max.	
R_{25}	Resistance	T_C =25°C	-	5	-	kΩ
ΔR/R	Deviation of R100	T_C =100°C, R_{100} =493Ω	5	-	5	%
P_{25}	Power dissipation	T_C =25°C	-	-	20	mW
$B_{25/50}$	B-value	R2 =R25 exp [$B_{25/50}$(1/T2 - 1/(298,15 K))]	-	3375	-	K
$B_{25/80}$	B-value	R2 =R25 exp [$B_{25/80}$(1/T2 - 1/(298,15 K))]	-	3411	-	K
$B_{25/100}$	B-value	R2 =R25 exp [$B_{25/100}$(1/T2 - 1/(298,15 K))]	-	3433	-	K

MOSFET Electrical characteristics (T_j=25°C unless otherwise specified, chip)

Symbol	Item	Condition		Value			Unit
				Min.	Typ.	Max	
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS} =0V, I_D =200uA		1200	-	-	V
I_{DSS}	Zero gate voltage drain Current	V_{DS} =1200V, V_{GS} =0V		-	2	-	μA
$V_{GS(th)}$	Gate-source threshold Voltage	I_D =70mA, V_{DS} =V_{GS}, T_j =25°C		1.8	2.7	-	V
		I_D =70mA, V_{DS} =V_{GS}, T_j =175°C		-	2.05	-	V
I_{GSS}	Gate-Source Leakage Current	V_{GS} =20V, V_{DS} =0V, T_j =25°C		-	200	-	nA
$R_{DS(on)}$ (Chip)	Static drain-source On-state resistance	I_D =150A, V_{GS} =15V	T_j =25°C	-	10.1	13.1	mΩ
			T_j =175°C	-	14.8	-	mΩ
$V_{DS(on)}$ (Chip)	Static drain-source On-state Voltage	I_D =150A, V_{GS} =15V	T_j =25°C	-	1.52	1.97	V
			T_j =175°C	-	2.22	-	V
C_{iss}	Input Capacitance	V_D =800V, V_{GS} =0V f =1MHz, V_{AC} =25mV		-	11.6	-	nF
C_{oss}	Output Capacitance			-	0.352	-	nF
C_{rss}	Reverse transfer Capacitance			-	0.028	-	nF
Q_G	Total gate charge	V_{DD}=800V, I_D=120A, V_{GS}=-5/+15V		-	360	-	nC
R_{Gint}	Internal Gate Resistance	f =1Mhz, V_{AC} =25mV		-	0.65	-	Ω
$t_{d(on)}$	Turn-on delay time	V_{DD} =600V, I_D =150A, V_{GS} =-5/+15V, R_G =5.1Ω, Inductive load switching operation	T_j =25°C	-	32	-	ns
			T_j =150°C	-	29	-	
t_r	Rise time		T_j =25°C	-	17	-	ns
			T_j =150°C	-	18	-	
$t_{d(off)}$	Turn-off delay time		T_j =25°C	-	102	-	ns
			T_j =150°C	-	118	-	
t_f	Fall time		T_j =25°C	-	37	-	ns
			T_j =150°C	-	43	-	
E_{on}	Turn-on power dissipation		T_j =25°C	-	3.32	-	mJ
			T_j =150°C	-	3.64	-	
E_{off}	Turn-off power dissipation		T_j =25°C	-	1.60	-	mJ
			T_j =150°C	-	1.73	-	
$R_{th(j-c)}$	FET Thermal Resistance	Junction to Case/MOSFET		-	0.14	-	K/W
$R_{th(c-f)}$	Contact thermal resistance	With thermal conductive grease /MOSFET		-	0.12	-	K/W

Assumes Thermal Conductivity of grease is 2.8 W/m・K and thickness is 50um.

Body Diode Electrical characteristics (T_j=25°C unless otherwise specified, chip: Target)

Symbol	Item	Condition		Value			Unit
				Min.	Typ.	Max	
V_{SD}	Body Diode Forward Voltage	V_{GS} =-5V I_{SD} =150A	T_j=25°C	-	5.5	-	V
			T_j=175°C	-	5.05	-	
T_{rr}	Reverse recovery time	V_{DD}=600V I_D=150A V_{GS}=-5/+15V R_G=5.1Ω Inductive load switching operation	T_j=25°C	-	58	-	ns
			T_j=150°C	-	47	-	
Q_{rr}	Reverse recovery charge		T_j=25°C	-	2.23	-	µC
			T_j=150°C	-	4.53	-	
E_{rr}	Diode switching power dissipation		T_j=25°C	-	0.63	-	mJ
			T_j=150°C	-	1.38	-	

Test Conditions

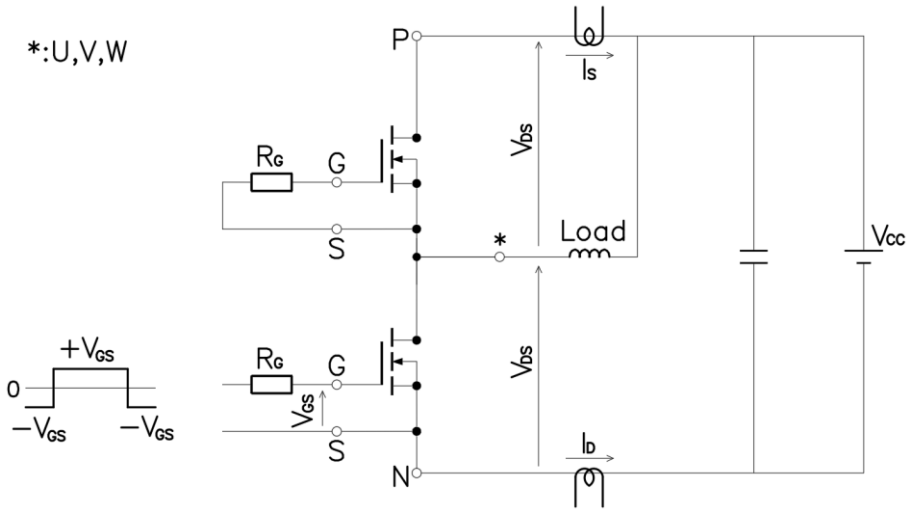


Figure 3. Switching time measure circuit

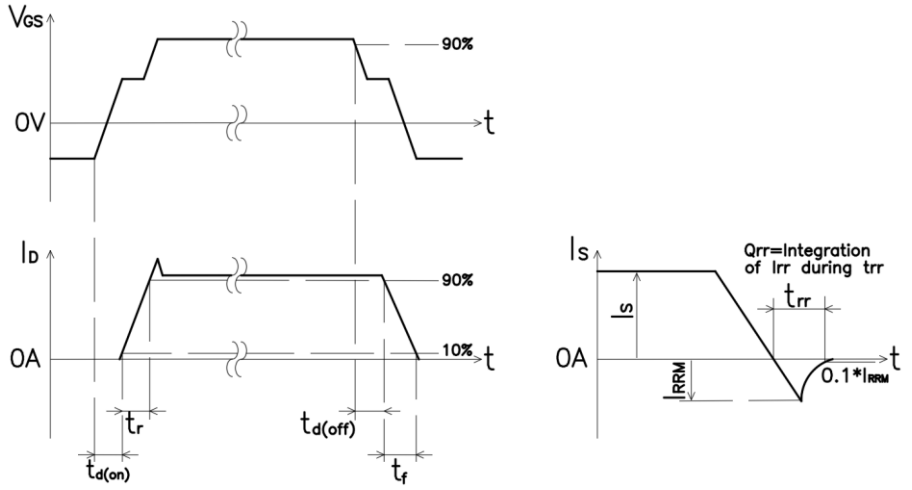


Figure 4. Switching time definition

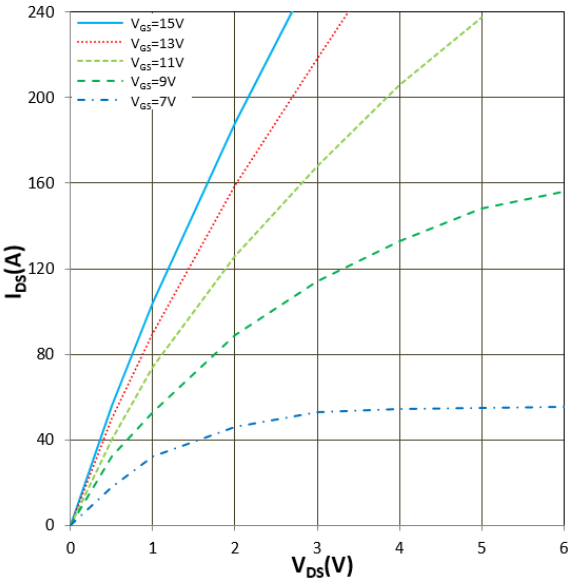


Figure 5. I_{DS} vs V_{DS}
T_j =25°C, V_{GS} parameter

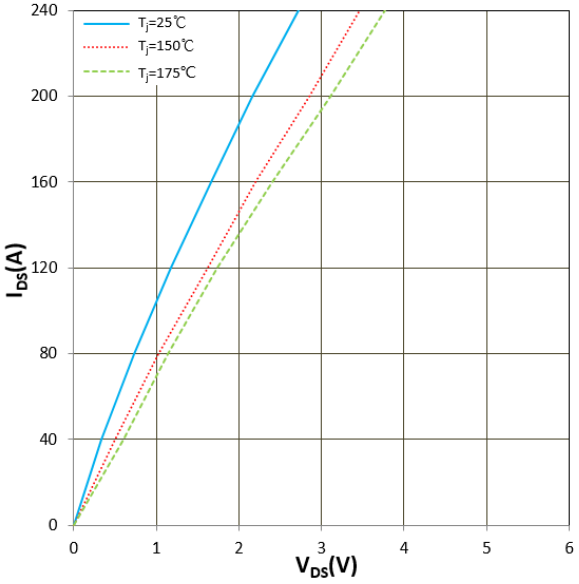


Figure 6. I_{DS} vs V_{DS}
V_{GS} =+15V

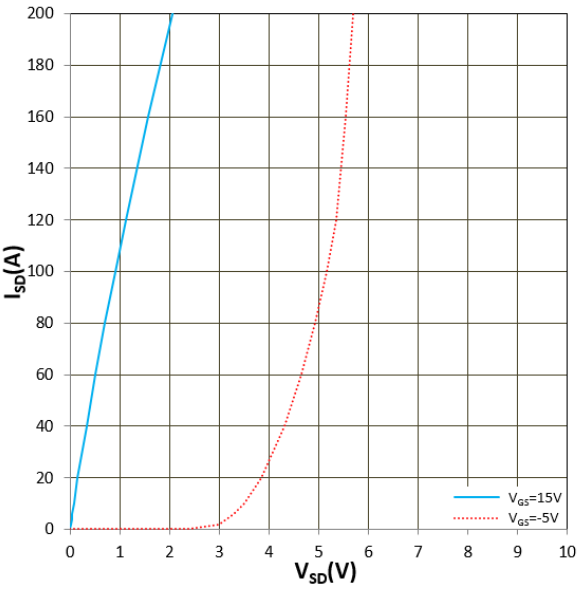


Figure 7. I_{SD} vs V_{SD} (V_F)
T_j =25°C, V_{GS} parameter

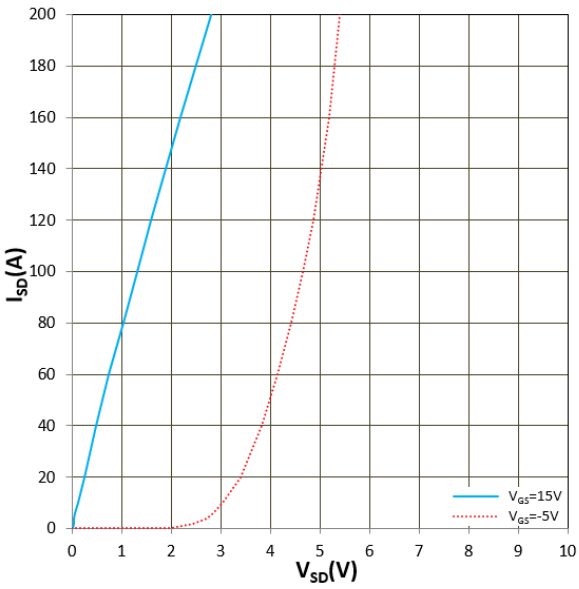


Figure8. I_{SD} vs V_{SD} (V_F)
T_j =175°C, V_{GS} parameter

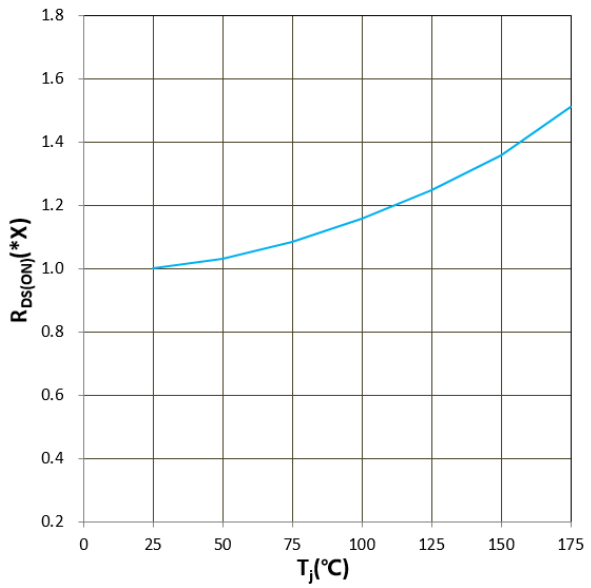


Figure 9. $R_{DS(ON)}$ vs T_j
V_{GS} =+15V, I_D =150A, 1.0X =10.1mΩ

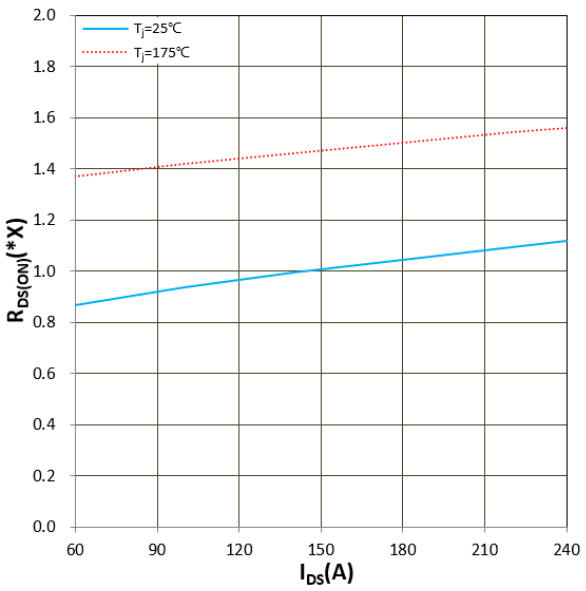


Figure 10. $R_{DS(ON)}$ vs I_{DS}
V_{GS} =+15V, 1.0X =10.1mΩ

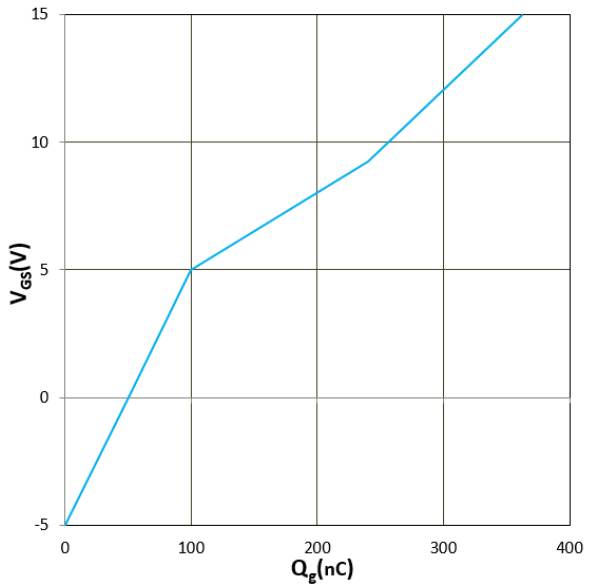


Figure 11. V_{GS} vs Q_g
V_{DS} =800V, I_D =120A , T_j =25°C

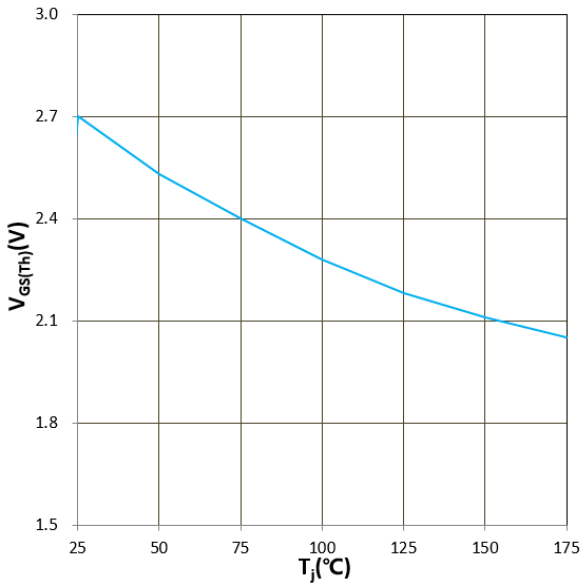


Figure 12. $V_{GS(TH)}$ vs T_j
V_{GS} =V_{DS}, I_D =70mA

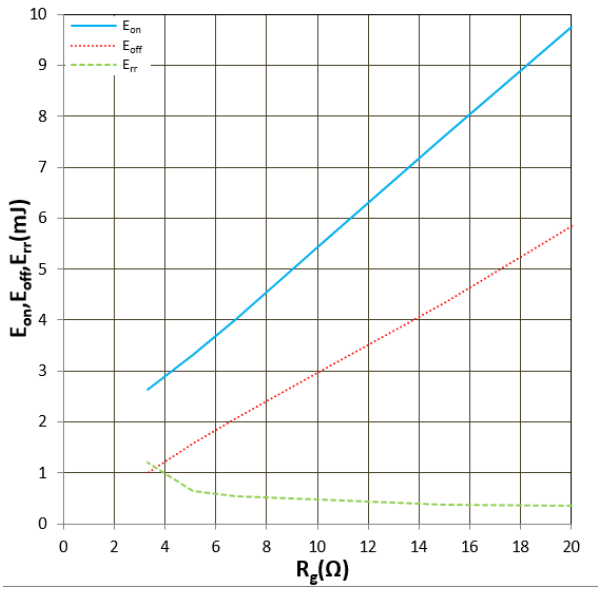


Figure 13. E_{on}, E_{off}, E_{rr} vs R_G
T_j =25°C, V_{CC} =600V, I_D =150A, V_{GS} =-5V/+15V
Inductive Load

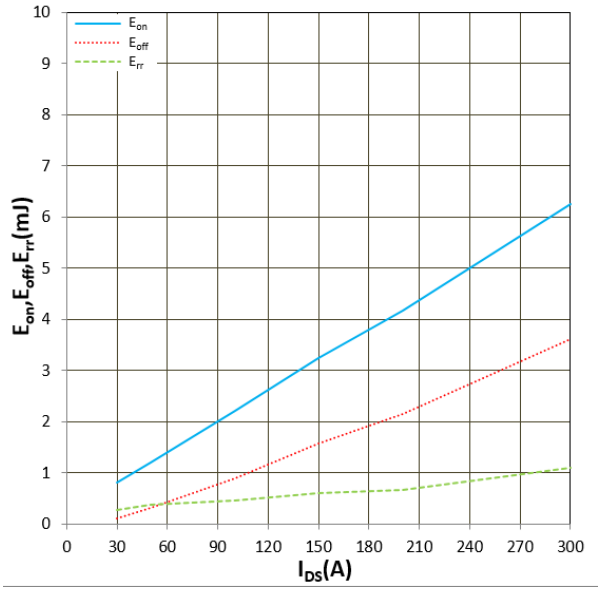


Figure 14. E_{on}, E_{off}, E_{rr} vs I_{DS}
T_j =25°C, V_{CC} =600V, R_G =5.1Ω, V_{GS} =-5V/+15V
Inductive Load

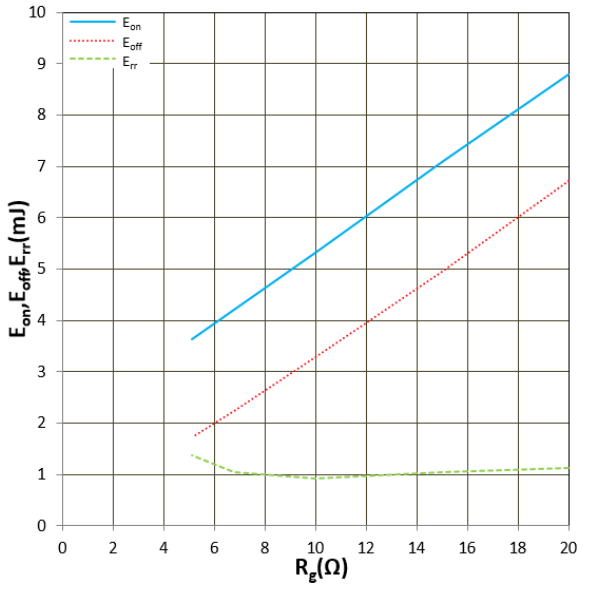


Figure 15. E_{on}, E_{off}, E_{rr} vs R_G
T_j =150°C, V_{CC} =600V, I_D =150A , V_{GS} =-5V/+15V
Inductive Load

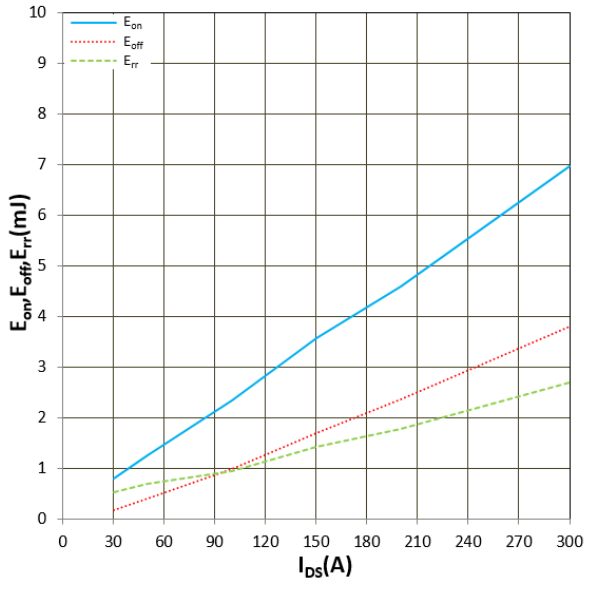
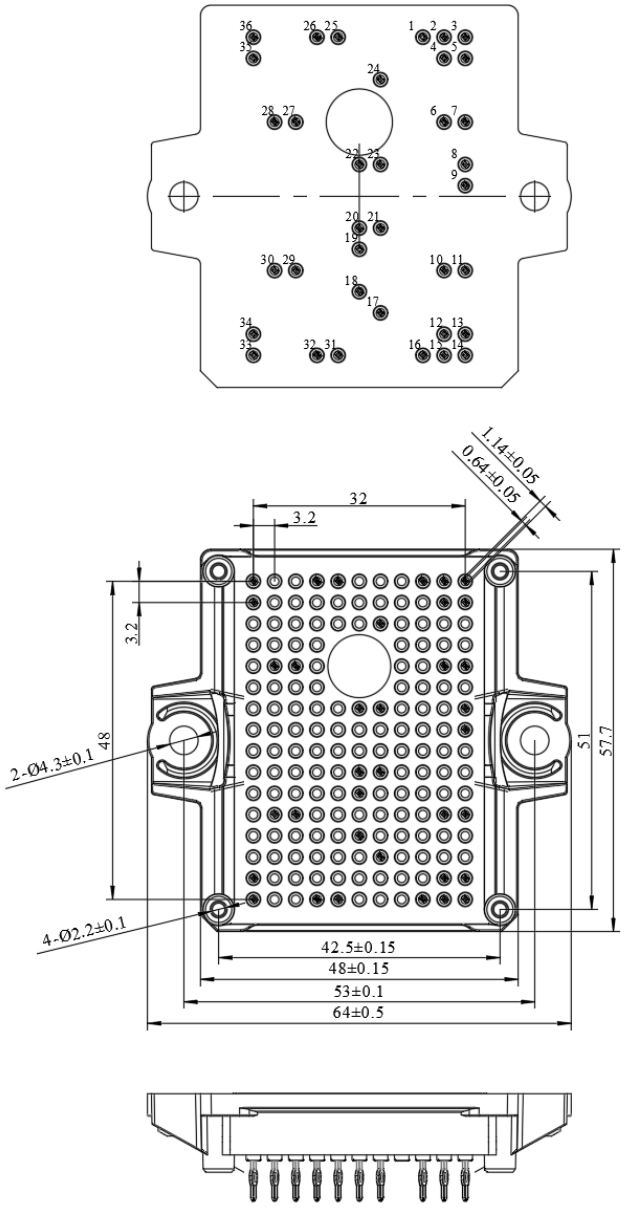


Figure 16. E_{on}, E_{off}, E_{rr} vs I_{DS}
T_j =150°C, V_{CC} =600V, R_G =5.1Ω, V_{GS} =-5V/+15V
Inductive Load

Package dimensions



Pin	X	Y
1	25,6	48
2	28,8	48
3	32	48
4	28,8	44,8
5	32	44,8
6	28,8	35,2
7	32	35,2
8	32	28,8
9	32	25,6
10	28,8	12,8
11	32	12,8
12	28,8	3,2
13	32	3,2
14	32	0
15	28,8	0
16	25,6	0
17	19,2	6,4
18	16	9,6
19	16	16
20	16	19,2
21	19,2	19,2
22	16	28,8
23	19,2	28,8
24	19,2	41,6
25	12,8	48
26	9,6	48
27	6,4	35,2
28	3,2	35,2
29	6,4	12,8
30	3,2	12,8
31	12,8	0
32	9,6	0
33	0	0
34	0	3,2
35	0	44,8
36	0	48

Unit: mm

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This product data sheet describes the characteristics of this product for which a warranty is granted. Any such warranty is granted exclusively under the terms and conditions of the supply agreement. There will be no guarantee or of any kind for the product and its characteristics.

The data contained in this document is exclusively intended for technically trained staff. You and your technical departments will have to evaluate the product's suitability for the intended application and the completeness of the product data concerning such application.

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